

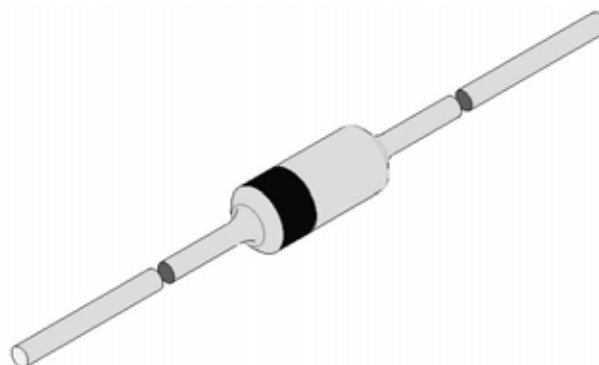
Schottky Barrier Diode

Features

1. High reliability
2. Low reverse current and low forward voltage

Applications

Low current rectification and high speed switching



Construction

Silicon epitaxial planar

Absolute Maximum Ratings

$T_j=25$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		1N60	V_{RRM}	40	V
		1N60P	V_{RRM}	45	V
Peak forward surge current	t_p 1 s	1N60	I_{FSM}	150	mA
		1N60P	I_{FSM}	500	mA
Forward continuous current	$T_a=25$	1N60	I_F	30	mA
		1N60P	I_F	50	mA
Storage temperature range			T_{stg}	-65~+125	

Maximum Thermal Resistance

$T_j=25$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50mm x 50mm x 1.6mm	R_{thJA}	250	K/W

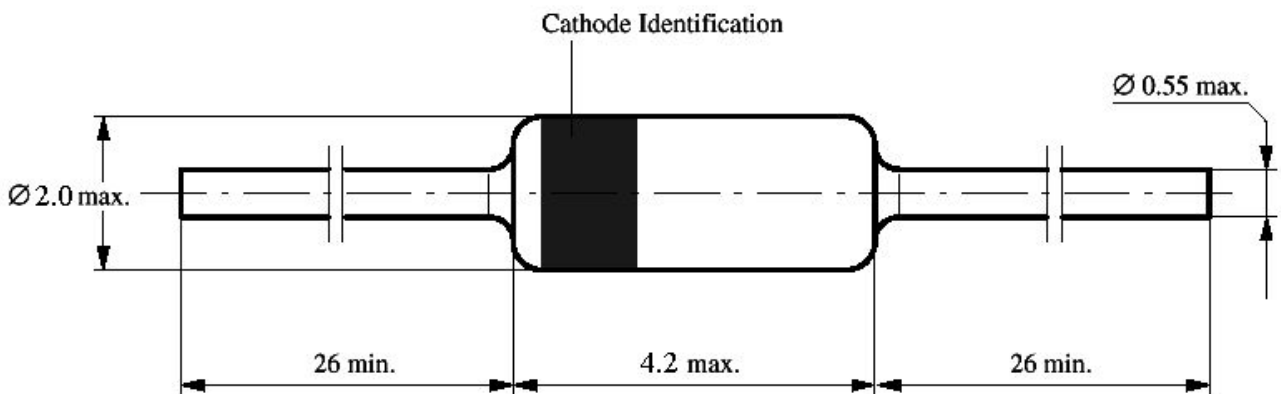
Formosa MicroSemi CO., LTD.

Electrical Characteristics

$T_j=25$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=1mA$	1N60	V_F		0.32	0.5	V
		1N60P	V_F		0.24	0.5	V
	$I_F=30mA$	1N60	V_F		0.65	1.0	V
	$I_F=200mA$	1N60P	V_F		0.65	1.0	V
Reverse current	$V_R=15V$	1N60	I_R		0.1	0.5	μA
		1N60P	I_R		0.5	1.0	μA
Junction capacitance	$V_R=1V, f=1MHz$	1N60	C_J		2.0		pF
	$V_R=10V, f=1MHz$	1N60P	C_J		6.0		pF
Reverse recovery time	$I_F=I_R=1mA, I_{tr}=1mA, R_C=100\Omega$		t_{rr}			1.0	ns

Dimensions in mm



Standard Glass Case
JEDEC DO 35